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	INFORMATION DISCLOSURE STATEMENT						PCT/JP2004/017562		
(Use several sheets if necessary)					APPLICANT Masateru NAKAMURA				
					FILING DATE January 31, 2006				
		U.	S. PATEN	T DOCUM	IENTS				
Examiner Initials	Cite No.	Document Number	Da	te	Name				
	I.	US 4,349,407	9/14/198	2	Lundberg				
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	2.	JP A 2000-264790	9/26/2000		JAPAN		x	x	
	3.	JP A 2004-315281			JAPAN		x	x	
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	4.	Hoffman, D. H., et al. "Prospects of the use of liquid phase techniques for the growth of bulk silicon carbide crystals" MATERIALS SCIENCE AND ENGINEERING B, ELSEVIER SEQUOLA, LAUSANNE, CH, vol. 61-62, 30 July 1999 (1999-07-30), pages 29-39, XP004363298 ISSN: 0921-5107.							
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